

BFP420F

Low Noise Silicon Bipolar RF Transistor

Data Sheet

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Page	Subjects (major changes since last revision)
	This datasheet replaces the revision from 20 April 2007. The product itself has not been changed and the device characteristics remain unchanged. Only the product description and information available in the datasheet has been expanded and updated.

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Table of Contents

	Table of Contents	4
	List of Figures	5
	List of Tables	6
1	Features	7
2	Maximum Ratings	8
3	Thermal Characteristics	9
4	Electrical Characteristics	10
4.1	DC Characteristics	10
4.2	General AC Characteristics	10
4.3	Frequency Dependent AC Characteristics	11
4.4	Characteristic DC Diagrams	18
4.5	Characteristic AC Diagrams	21
5	Simulation Data	28
6	Package Information TSFP-4	29

List of Figures

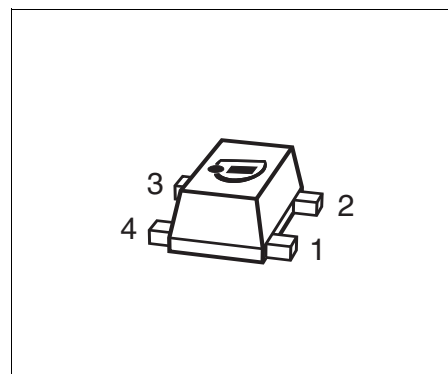
Figure 1	Total Power Dissipation $P_{\text{tot}} = f(T_s)$	9
Figure 2	Testing Circuit.	11
Figure 3	Collector Current vs. Collector Emitter Voltage $I_C = f(V_{CE})$, $I_B = \text{Parameter}$	18
Figure 4	DC Current Gain $h_{FE} = f(I_C)$, $V_{CE} = 3 \text{ V}$	18
Figure 5	Collector Current vs. Base Emitter Voltage $I_C = f(V_{BE})$, $V_{CE} = 3 \text{ V}$	19
Figure 6	Base Current vs. Base Emitter Forward Voltage $I_B = f(V_{BE})$, $V_{CE} = 3 \text{ V}$	19
Figure 7	Base Current vs. Base Emitter Reverse Voltage $I_B = f(V_{EB})$, $V_{CE} = 3 \text{ V}$	20
Figure 8	Collector Emitter Breakdown Voltage $V_{CER} = f(R_{BE})$, $I_C = 1 \text{ mA}$	20
Figure 9	Transition Frequency $f_T = f(I_C)$, $f = 2 \text{ GHz}$, $V_{CE} = \text{Parameter}$	21
Figure 10	3rd Order Intercept Point $OIP_3 = f(I_C)$, $Z_S = Z_L = 50 \Omega$, V_{CE} , $f = \text{Parameters}$	21
Figure 11	3rd Order Intercept Point at output $OIP_3 [\text{dBm}] = f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 1900 \text{ MHz}$	22
Figure 12	Compression Point at output $OP_{1dB} [\text{dBm}] = f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 1900 \text{ MHz}$	22
Figure 13	Collector Base Capacitance $C_{CB} = f(V_{CB})$, $f = 1 \text{ MHz}$	23
Figure 14	Gain G_{ma} , G_{ms} , $ S_{21} ^2 = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 15 \text{ mA}$	23
Figure 15	Maximum Power Gain $G_{\text{max}} = f(I_C)$, $V_{CE} = 3 \text{ V}$, $f = \text{Parameter in GHz}$	24
Figure 16	Maximum Power Gain $G_{\text{max}} = f(V_{CE})$, $I_C = 15 \text{ mA}$, $f = \text{Parameter in GHz}$	24
Figure 17	Input Matching $S_{11} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 / 45 \text{ mA}$	25
Figure 18	Source Impedance for Minimum Noise Figure $Z_{\text{opt}} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 \text{ mA}$	25
Figure 19	Output Matching $S_{22} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 / 45 \text{ mA}$	26
Figure 20	Noise Figure $NF_{\text{min}} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 \text{ mA}$, $Z_S = Z_{\text{opt}}$	26
Figure 21	Noise Figure $NF_{\text{min}} = f(I_C)$, $V_{CE} = 3 \text{ V}$, $Z_S = Z_{\text{opt}}$, $f = \text{Parameter in GHz}$	27
Figure 22	Noise Figure $NF_{50} = f(I_C)$, $V_{CE} = 3 \text{ V}$, $Z_S = 50 \Omega$, $f = \text{Parameter in GHz}$	27
Figure 23	Package Outline	29
Figure 24	Package Foot Print	29
Figure 25	Marking Example (Marking BFP420F: AMs)	29
Figure 26	Tape Dimensions	29

List of Tables

Table 1	Maximum Ratings at $T_A = 25^\circ\text{C}$ (unless otherwise specified)	8
Table 2	Thermal Resistance	9
Table 3	DC Characteristics at $T_A = 25^\circ\text{C}$	10
Table 4	General AC Characteristics at $T_A = 25^\circ\text{C}$	10
Table 5	AC Characteristics, $f = 150\text{ MHz}$	11
Table 6	AC Characteristics, $f = 450\text{ MHz}$	12
Table 7	AC Characteristics, $f = 900\text{ MHz}$	12
Table 8	AC Characteristics, $f = 1500\text{ MHz}$	13
Table 9	AC Characteristics, $f = 1900\text{ MHz}$	14
Table 10	AC Characteristics, $f = 2400\text{ MHz}$	15
Table 11	AC Characteristics, $f = 3500\text{ MHz}$	15
Table 12	AC Characteristics, $f = 5500\text{ MHz}$	16

1 Features

- Low noise high gain silicon bipolar RF transistor
- Based on Infineon's reliable very high volume 25 GHz silicon bipolar technology
- 0.9 dB minimum noise figure typical at 900 MHz, 3 V, 4 mA
- 16 dB maximum gain (G_{ma}) typical at 2.4 GHz, 3 V, 15 mA
- 28 dBm OIP_3 typical at 2.4 GHz, 4 V, 40 mA
- 16.5 dBm OP_{1dB} typical at 2.4 GHz, 4 V, 40 mA
- Popular in discrete oscillators
- Thin, small, flat, Pb-free (RoHS compliant) and Hal-free ("green") package with visible leads



TSFP-4-1



Applications

As Low Noise Amplifier (LNA) in

- Satellite communication systems: Navigation systems (GPS, Glonass), satellite radio (SDARs, DAB)
- Multimedia applications such as mobile/portable TV, CATV, FM Radio
- ISM applications like RKE, AMR and Zigbee

As discrete active mixer in RF Frontends

As active device in discrete oscillators

Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions

Product Name	Package	Pin Configuration				Marking
BFP420F	TSFP-4-1	1 = B	2 = E	3 = C	4 = E	AMs

2 Maximum Ratings

Table 1 Maximum Ratings at $T_A = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Collector emitter voltage	V_{CEO}	–	4.5	V	Open base $T_A = 25^\circ\text{C}$
		–	4.1	V	$T_A = -55^\circ\text{C}$
Collector base voltage	V_{CBO}	–	15	V	Open emitter
Collector emitter voltage	V_{CES}	–	15	V	Emitter / base shortened
Emitter base voltage	V_{EBO}	–	1.5	V	Open collector
Base current	I_{B}		9	mA	–
Collector current	I_{C}	–	60	mA	–
RF input power	P_{RFIn}	–	–	dBm	–
Total power dissipation ¹⁾	P_{tot}	–	210	mW	$T_S \leq 100^\circ\text{C}$
Junction temperature	T_{J}	–	150	$^\circ\text{C}$	–
Storage temperature	T_{Stg}	-55	150	$^\circ\text{C}$	–

1) T_S is the soldering point temperature. T_S measured on the emitter lead at the soldering point of the pcb.

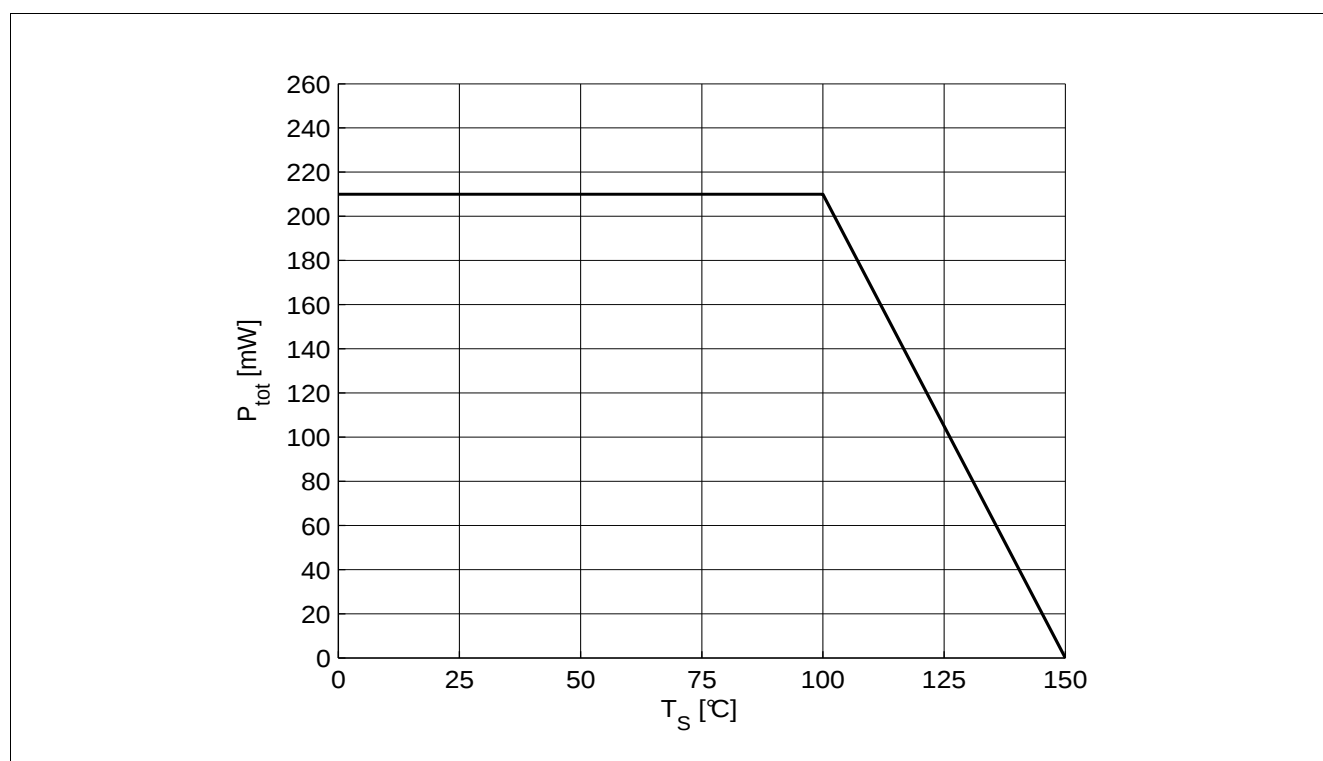
Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

3 Thermal Characteristics

Table 2 Thermal Resistance

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Junction - soldering point ¹⁾	R_{thJS}	–	240	–	K/W	–

1) For calculation of R_{thJA} please refer to Application Note Thermal Resistance AN 077


Figure 1 Total Power Dissipation $P_{tot} = f(T_s)$

4 Electrical Characteristics

4.1 DC Characteristics

Table 3 DC Characteristics at $T_A = 25\text{ °C}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	4.5	5.5	–	V	$I_C = 1\text{ mA}$, $I_B = 0$ Open base
Collector emitter leakage current	I_{CES}	–	–	10	μA	$V_{CE} = 15\text{ V}$, $V_{BE} = 0$
		–	1	30	nA	$V_{CE} = 3\text{ V}$, $V_{BE} = 0$ Emitter/base shorted
Collector base leakage current	I_{CBO}	–	1	30	nA	$V_{CB} = 3\text{ V}$, $I_E = 0$ Open emitter
Emitter base leakage current	I_{EBO}	–	10	100	nA	$V_{EB} = 0.5\text{ V}$, $I_C = 0$ Open collector
DC current gain	h_{FE}	60	95	130		$V_{CE} = 4\text{ V}$, $I_C = 5\text{ mA}$ Pulse measured

4.2 General AC Characteristics

Table 4 General AC Characteristics at $T_A = 25\text{ °C}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Transition frequency	f_T	18	25	–	GHz	$V_{CE} = 3\text{ V}$, $I_C = 30\text{ mA}$ $f = 2\text{ GHz}$
Collector base capacitance	C_{CB}	–	0.15	0.3	pF	$V_{CB} = 2\text{ V}$, $V_{BE} = 0$ $f = 1\text{ MHz}$ Emitter grounded
Collector emitter capacitance	C_{CE}	–	0.46	–	pF	$V_{CE} = 2\text{ V}$, $V_{BE} = 0$ $f = 1\text{ MHz}$ Base grounded
Emitter base capacitance	C_{EB}	–	0.55	–	pF	$V_{EB} = 0.5\text{ V}$, $V_{CB} = 0$ $f = 1\text{ MHz}$ Collector grounded

4.3 Frequency Dependent AC Characteristics

Measurement setup is a test fixture with Bias T's in a $50\ \Omega$ system, $T_A = 25\ ^\circ\text{C}$

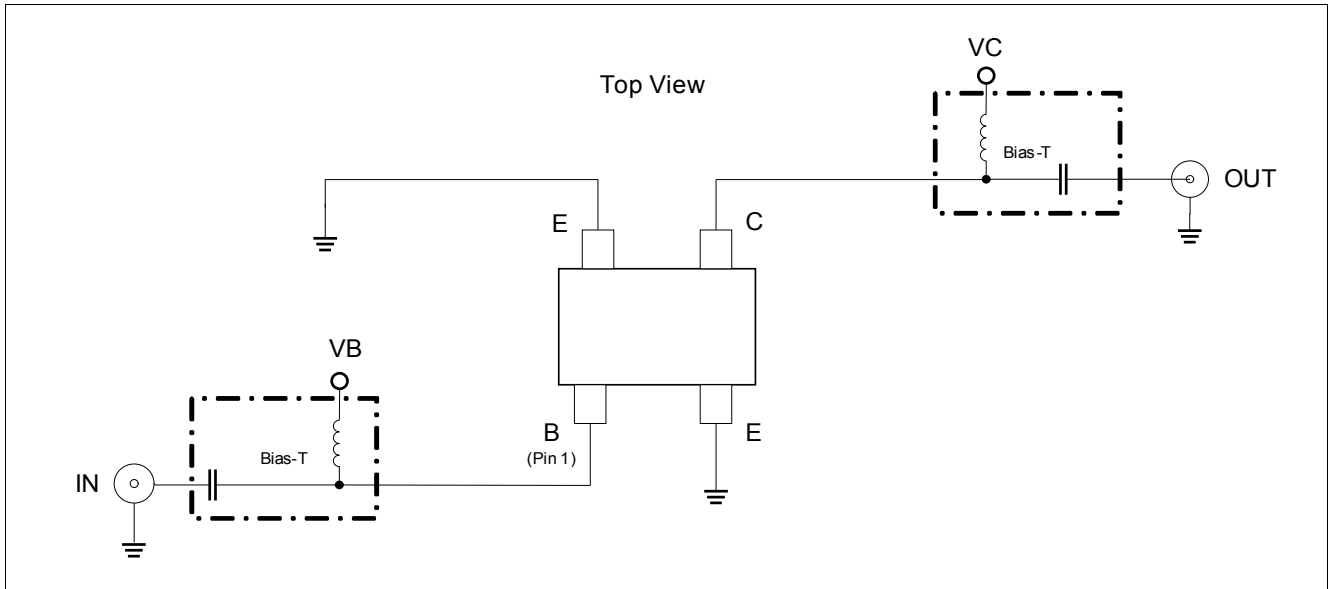


Figure 2 Testing Circuit

Table 5 AC Characteristics, $f = 150\ \text{MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain						
@ low noise operating point	G_{ms}	—	30	—	dB	$Z_S = Z_{SoptG}$, $Z_L = Z_{LoptG}$ $V_{CE} = 3\ \text{V}$, $I_C = 4\ \text{mA}$
@ recommended trade off oper. point	G_{ms}	—	34.5	—		$V_{CE} = 3\ \text{V}$, $I_C = 15\ \text{mA}$
@ max. linearity operating point	G_{ms}	—	37	—		$V_{CE} = 4\ \text{V}$, $I_C = 40\ \text{mA}$
Transducer gain						
@ low noise operating point	S_{21}	—	22	—	dB	$Z_S = Z_L = 50\ \Omega$ $V_{CE} = 3\ \text{V}$, $I_C = 4\ \text{mA}$
@ recommended trade off oper. point	S_{21}	—	30	—		$V_{CE} = 3\ \text{V}$, $I_C = 15\ \text{mA}$
@ max. linearity operating point	S_{21}	—	33	—		$V_{CE} = 4\ \text{V}$, $I_C = 40\ \text{mA}$
Noise figure						
@ low noise operating point					dB	$Z_S = Z_{SoptN}$ $V_{CE} = 3\ \text{V}$, $I_C = 4\ \text{mA}$
Minimum noise figure	NF_{min}	—	0.9	—		
Associated gain	G_{ass}	—	24	—		
@ recommended trade off oper. point						$V_{CE} = 3\ \text{V}$, $I_C = 15\ \text{mA}$
Minimum noise figure	NF_{min}	—	1.4	—		
Associated gain	G_{ass}	—	29	—		
Linearity						
@ recommended trade off oper. point					dBm	$Z_S = Z_L = 50\ \Omega$ $V_{CE} = 3\ \text{V}$, $I_C = 15\ \text{mA}$
3rd order intercept point at output	OIP_3	—	21	—		
1 dB gain compression point at output	OP_{1dB}	—	7	—		

Electrical Characteristics

Table 5 AC Characteristics, $f = 150$ MHz (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
@ max. linearity operating point						$V_{CE} = 4$ V, $I_C = 40$ mA
3rd order intercept point at output	OIP_3	–	25	–		
1 dB gain compression point at output	OP_{1dB}	–	15.5	–		

Table 6 AC Characteristics, $f = 450$ MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	$Z_S = Z_{SoptG}$, $Z_L = Z_{LoptG}$
@ low noise operating point	G_{ms}	–	25	–		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	G_{ms}	–	29	–		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	G_{ms}	–	31	–		$V_{CE} = 4$ V, $I_C = 40$ mA
Transducer gain					dB	$Z_S = Z_L = 50$ Ω
@ low noise operating point	S_{21}	–	21	–		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	S_{21}	–	27	–		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	S_{21}	–	28.5	–		$V_{CE} = 4$ V, $I_C = 40$ mA
Noise figure					dB	$Z_S = Z_{SoptN}$
@ low noise operating point						$V_{CE} = 3$ V, $I_C = 4$ mA
Minimum noise figure	NF_{min}	–	0.9	–		
Associated gain	G_{ass}	–	22.5	–		
@ recommended trade off oper. point						$V_{CE} = 3$ V, $I_C = 15$ mA
Minimum noise figure	NF_{min}	–	1.4	–		
Associated gain	G_{ass}	–	27	–		
Linearity					dBm	$Z_S = Z_L = 50$ Ω
@ recommended trade off oper. point						$V_{CE} = 3$ V, $I_C = 15$ mA
3rd order intercept point at output	OIP_3	–	21.5	–		
1 dB gain compression point at output	OP_{1dB}	–	8	–		
@ max. linearity operating point						$V_{CE} = 4$ V, $I_C = 40$ mA
3rd order intercept point at output	OIP_3	–	26.5	–		
1 dB gain compression point at output	OP_{1dB}	–	16.5	–		

Table 7 AC Characteristics, $f = 900$ MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	$Z_S = Z_{SoptG}$, $Z_L = Z_{LoptG}$
@ low noise operating point	G_{ms}	–	22	–		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	G_{ms}	–	25	–		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	G_{ms}	–	26.5	–		$V_{CE} = 4$ V, $I_C = 40$ mA

Electrical Characteristics

Table 7 AC Characteristics, $f = 900 \text{ MHz}$ (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Transducer gain					dB	$Z_S = Z_L = 50 \Omega$
@ low noise operating point	S_{21}	–	19	–		$V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
@ recommended trade off oper. point	S_{21}	–	23	–		$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ max. linearity operating point	S_{21}	–	24	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
Noise figure					dB	$Z_S = Z_{\text{SoptN}}$
@ low noise operating point						$V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
Minimum noise figure	$NF_{\min}$	–	0.95	–		
Associated gain	G_{ass}	–	20	–		
@ recommended trade off oper. point						$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
Minimum noise figure	$NF_{\min}$	–	1.4	–		
Associated gain	G_{ass}	–	23	–		
Linearity					dBm	$Z_S = Z_L = 50 \Omega$
@ recommended trade off oper. point						$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
3rd order intercept point at output	OIP_3	–	23.5	–		
1 dB gain compression point at output	$OP_{1\text{dB}}$	–	8	–		
@ max. linearity operating point						$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
3rd order intercept point at output	OIP_3	–	27.5	–		
1 dB gain compression point at output	$OP_{1\text{dB}}$	–	17	–		

Table 8 AC Characteristics, $f = 1500 \text{ MHz}$

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	$Z_S = Z_{\text{SoptG}}, Z_L = Z_{\text{LoptG}}$
@ low noise operating point	G_{ms}	–	19	–		$V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
@ recommended trade off oper. point	G_{ms}	–	22	–		$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ max. linearity operating point	G_{ma}	–	22	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
Transducer gain					dB	$Z_S = Z_L = 50 \Omega$
@ low noise operating point	S_{21}	–	16	–		$V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
@ recommended trade off oper. point	S_{21}	–	19	–		$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ max. linearity operating point	S_{21}	–	19.5	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
Noise figure					dB	$Z_S = Z_{\text{SoptN}}$
@ low noise operating point						$V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
Minimum noise figure	$NF_{\min}$	–	1	–		
Associated gain	G_{ass}	–	16.5	–		
@ recommended trade off oper. point						$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
Minimum noise figure	$NF_{\min}$	–	1.5	–		
Associated gain	G_{ass}	–	19	–		

Electrical Characteristics

Table 8 AC Characteristics, $f = 1500$ MHz (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Linearity					dBm	$Z_S = Z_L = 50 \Omega$ $V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ recommended trade off oper. point						
3rd order intercept point at output	OIP_3	–	22.5	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
1 dB gain compression point at output	OP_{1dB}	–	7	–		
@ max. linearity operating point						
3rd order intercept point at output	OIP_3	–	27.5	–		
1 dB gain compression point at output	OP_{1dB}	–	16	–		

Table 9 AC Characteristics, $f = 1900$ MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	$Z_S = Z_{SoptG}, Z_L = Z_{LoptG}$ $V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
@ low noise operating point	G_{ms}	–	18	–		
@ recommended trade off oper. point	G_{ma}	–	19.5	–		$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ max. linearity operating point	G_{ma}	–	19	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
Transducer gain					dB	$Z_S = Z_L = 50 \Omega$ $V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
@ low noise operating point	S_{21}	–	14	–		
@ recommended trade off oper. point	S_{21}	–	16.5	–		$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ max. linearity operating point	S_{21}	–	17	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
Noise figure					dB	$Z_S = Z_{SoptN}$ $V_{CE} = 3 \text{ V}, I_C = 4 \text{ mA}$
@ low noise operating point						
Minimum noise figure	NF_{min}	–	1.1	–		$V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
Associated gain	G_{ass}	–	15	–		
@ recommended trade off oper. point						
Minimum noise figure	NF_{min}	–	1.5	–		
Associated gain	G_{ass}	–	17	–		
Linearity					dBm	$Z_S = Z_L = 50 \Omega$ $V_{CE} = 3 \text{ V}, I_C = 15 \text{ mA}$
@ recommended trade off oper. point						
3rd order intercept point at output	OIP_3	–	24	–		$V_{CE} = 4 \text{ V}, I_C = 40 \text{ mA}$
1 dB gain compression point at output	OP_{1dB}	–	9	–		
@ max. linearity operating point						
3rd order intercept point at output	OIP_3	–	28	–		
1 dB gain compression point at output	OP_{1dB}	–	17	–		

Electrical Characteristics

Table 10 AC Characteristics, $f = 2400$ MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	$Z_S = Z_{SoptG}$, $Z_L = Z_{LoptG}$
@ low noise operating point	G_{ms}	—	16.5	—		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	G_{ma}	—	16.5	—		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	G_{ma}	—	16.5	—		$V_{CE} = 4$ V, $I_C = 40$ mA
Transducer gain					dB	$Z_S = Z_L = 50 \Omega$
@ low noise operating point	S_{21}	—	12	—		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	S_{21}	—	14.5	—		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	S_{21}	—	15	—		$V_{CE} = 4$ V, $I_C = 40$ mA
Noise figure					dB	$Z_S = Z_{SoptN}$
@ low noise operating point						$V_{CE} = 3$ V, $I_C = 4$ mA
Minimum noise figure	NF_{min}	—	1.2	—		
Associated gain	G_{ass}	—	12.5	—		
@ recommended trade off oper. point						$V_{CE} = 3$ V, $I_C = 15$ mA
Minimum noise figure	NF_{min}	—	1.6	—		
Associated gain	G_{ass}	—	15	—		
Linearity					dBm	$Z_S = Z_L = 50 \Omega$
@ recommended trade off oper. point						$V_{CE} = 3$ V, $I_C = 15$ mA
3rd order intercept point at output	OIP_3	—	24.5	—		
1 dB gain compression point at output	OP_{1dB}	—	8.5	—		
@ max. linearity operating point						$V_{CE} = 4$ V, $I_C = 40$ mA
3rd order intercept point at output	OIP_3	—	28	—		
1 dB gain compression point at output	OP_{1dB}	—	16.5	—		

Table 11 AC Characteristics, $f = 3500$ MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain					dB	$Z_S = Z_{SoptG}$, $Z_L = Z_{LoptG}$
@ low noise operating point	G_{ma}	—	11.5	—		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	G_{ma}	—	12.5	—		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	G_{ma}	—	13	—		$V_{CE} = 4$ V, $I_C = 40$ mA
Transducer gain					dB	$Z_S = Z_L = 50 \Omega$
@ low noise operating point	S_{21}	—	9	—		$V_{CE} = 3$ V, $I_C = 4$ mA
@ recommended trade off oper. point	S_{21}	—	11	—		$V_{CE} = 3$ V, $I_C = 15$ mA
@ max. linearity operating point	S_{21}	—	11.5	—		$V_{CE} = 4$ V, $I_C = 40$ mA
Noise figure					dB	$Z_S = Z_{SoptN}$
@ low noise operating point						$V_{CE} = 3$ V, $I_C = 4$ mA
Minimum noise figure	NF_{min}	—	1.6	—		

Electrical Characteristics

Table 11 AC Characteristics, $f = 3500$ MHz (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Associated gain @ recommended trade off oper. point	G_{ass}	–	10	–		$V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 15 \text{ mA}$
Minimum noise figure	NF_{min}	–	1.8	–		
Associated gain	G_{ass}	–	11.5	–		
Linearity @ recommended trade off oper. point					dBm	$Z_{\text{S}} = Z_{\text{L}} = 50 \Omega$ $V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 15 \text{ mA}$
3rd order intercept point at output	OIP_3	–	22	–		
1 dB gain compression point at output	$OP_{1\text{dB}}$	–	8	–		
@ max. linearity operating point						$V_{\text{CE}} = 4 \text{ V}, I_{\text{C}} = 40 \text{ mA}$
3rd order intercept point at output	OIP_3	–	26	–		
1 dB gain compression point at output	$OP_{1\text{dB}}$	–	17	–		

Table 12 AC Characteristics, $f = 5500$ MHz

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum power gain @ low noise operating point	G_{ma}	–	7.5	–	dB	$Z_{\text{S}} = Z_{\text{SoptG}}, Z_{\text{L}} = Z_{\text{LoptG}}$ $V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 4 \text{ mA}$
@ recommended trade off oper. point	G_{ma}	–	8.5	–		$V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 15 \text{ mA}$
@ max. linearity operating point	G_{ma}	–	9	–		$V_{\text{CE}} = 4 \text{ V}, I_{\text{C}} = 40 \text{ mA}$
Transducer gain @ low noise operating point	S_{21}	–	5.5	–	dB	$Z_{\text{S}} = Z_{\text{L}} = 50 \Omega$ $V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 4 \text{ mA}$
@ recommended trade off oper. point	S_{21}	–	7	–		$V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 15 \text{ mA}$
@ max. linearity operating point	S_{21}	–	8	–		$V_{\text{CE}} = 4 \text{ V}, I_{\text{C}} = 40 \text{ mA}$
Noise figure @ low noise operating point					dB	$Z_{\text{S}} = Z_{\text{SoptN}}$ $V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 4 \text{ mA}$
Minimum noise figure	NF_{min}	–	2.2	–		
Associated gain	G_{ass}	–	5	–		
@ recommended trade off oper. point						$V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 15 \text{ mA}$
Minimum noise figure	NF_{min}	–	2.3	–		
Associated gain	G_{ass}	–	8	–		
Linearity @ recommended trade off oper. point					dBm	$Z_{\text{S}} = Z_{\text{L}} = 50 \Omega$ $V_{\text{CE}} = 3 \text{ V}, I_{\text{C}} = 15 \text{ mA}$
3rd order intercept point at output	OIP_3	–	22	–		
1 dB gain compression point at output	$OP_{1\text{dB}}$	–	8.5	–		
@ max. linearity operating point						$V_{\text{CE}} = 4 \text{ V}, I_{\text{C}} = 40 \text{ mA}$
3rd order intercept point at output	OIP_3	–	26	–		
1 dB gain compression point at output	$OP_{1\text{dB}}$	–	17	–		

Note:

1. $G_{ms} = |S_{21}| / |S_{12}|$ for $k < 1$; $G_{ma} = |S_{21}| / |S_{12}|(k^2 - 1)^{1/2}$ for $k > 1$
2. In order to get the NF_{min} values stated in this chapter the test fixture losses have been subtracted from all measured results.
3. OIP_3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is $50\ \Omega$ from 0.2 MHz to 12 GHz.

4.4 Characteristic DC Diagrams

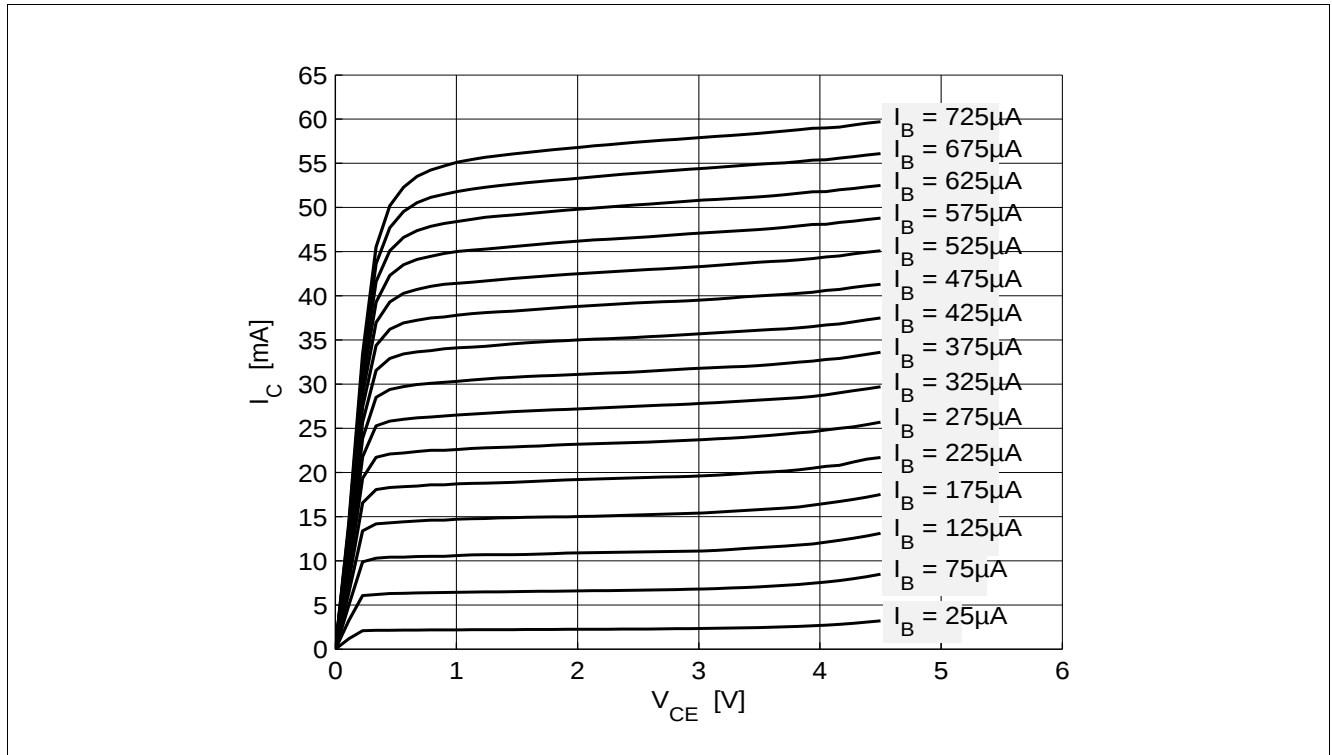


Figure 3 Collector Current vs. Collector Emitter Voltage $I_C = f(V_{CE})$, $I_B = \text{Parameter}$

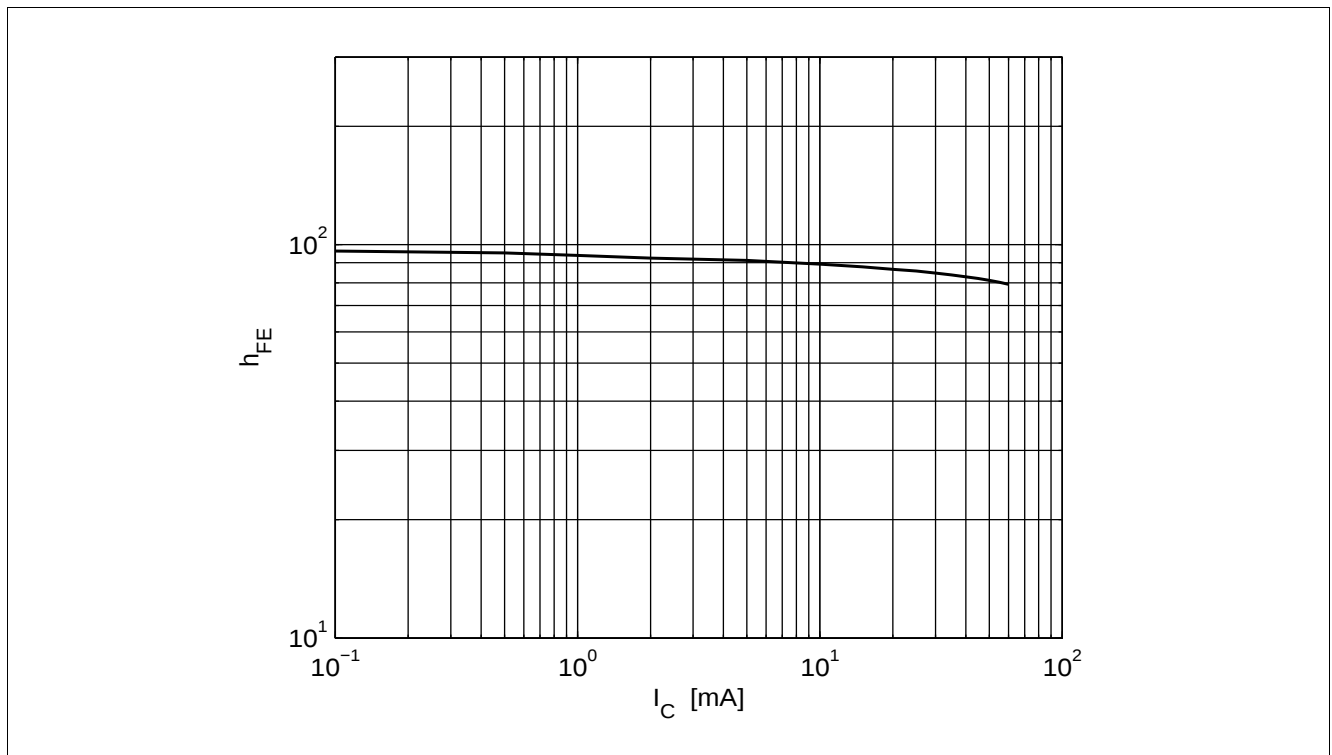


Figure 4 DC Current Gain $h_{FE} = f(I_C)$, $V_{CE} = 3 \text{ V}$

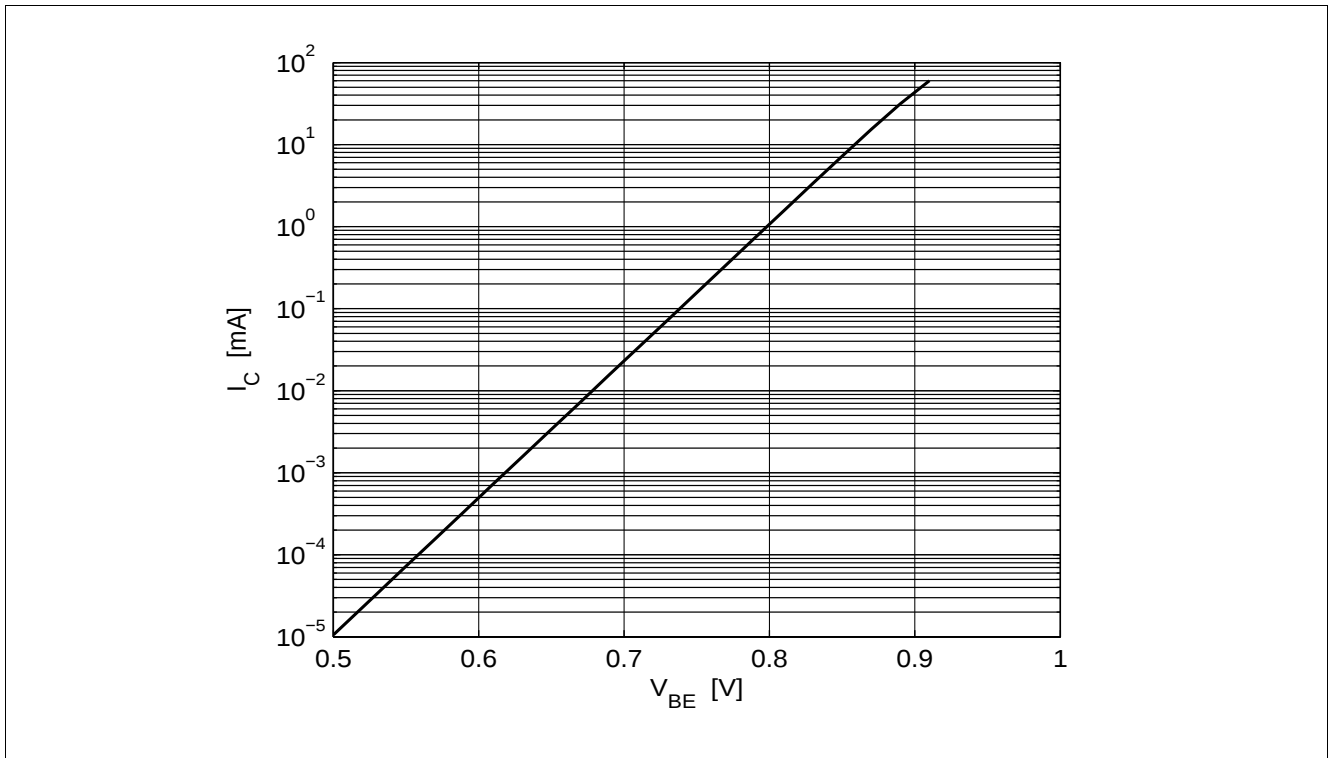


Figure 5 Collector Current vs. Base Emitter Voltage $I_C = f(V_{BE})$, $V_{CE} = 3\text{ V}$

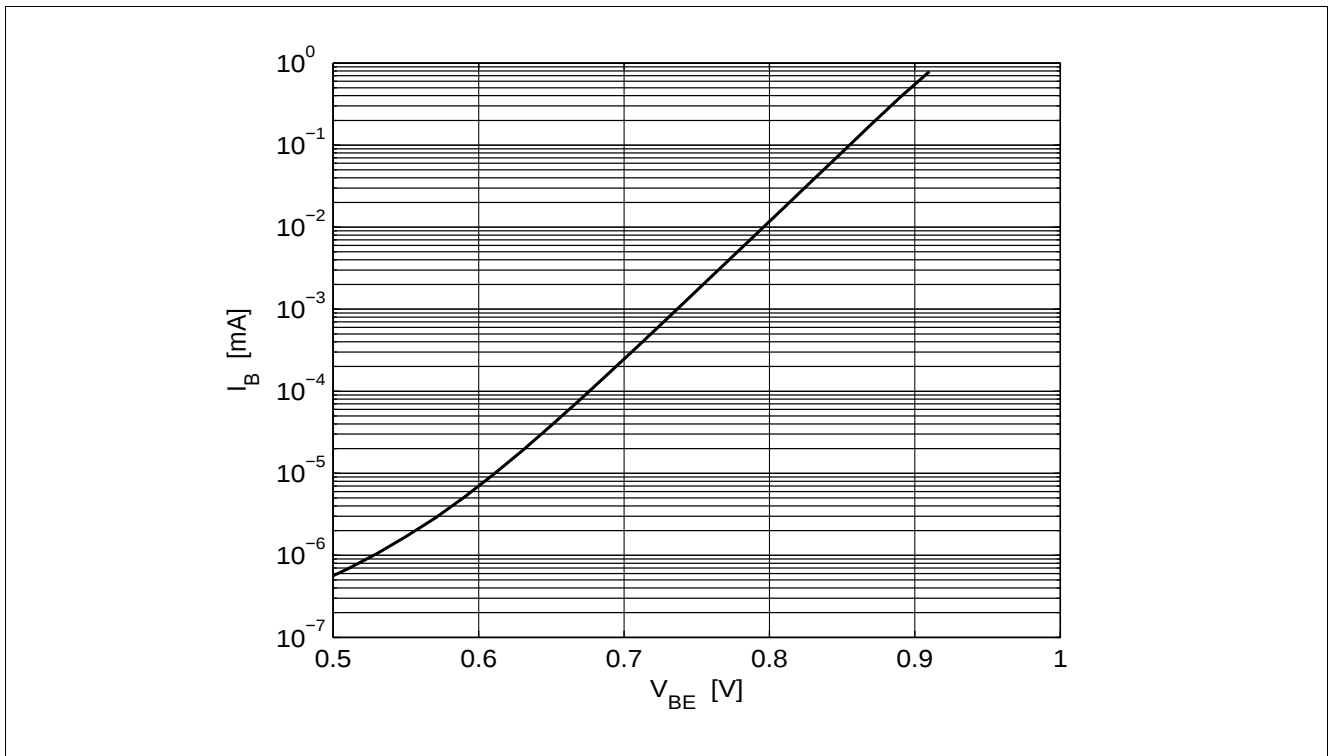


Figure 6 Base Current vs. Base Emitter Forward Voltage $I_B = f(V_{BE})$, $V_{CE} = 3\text{ V}$

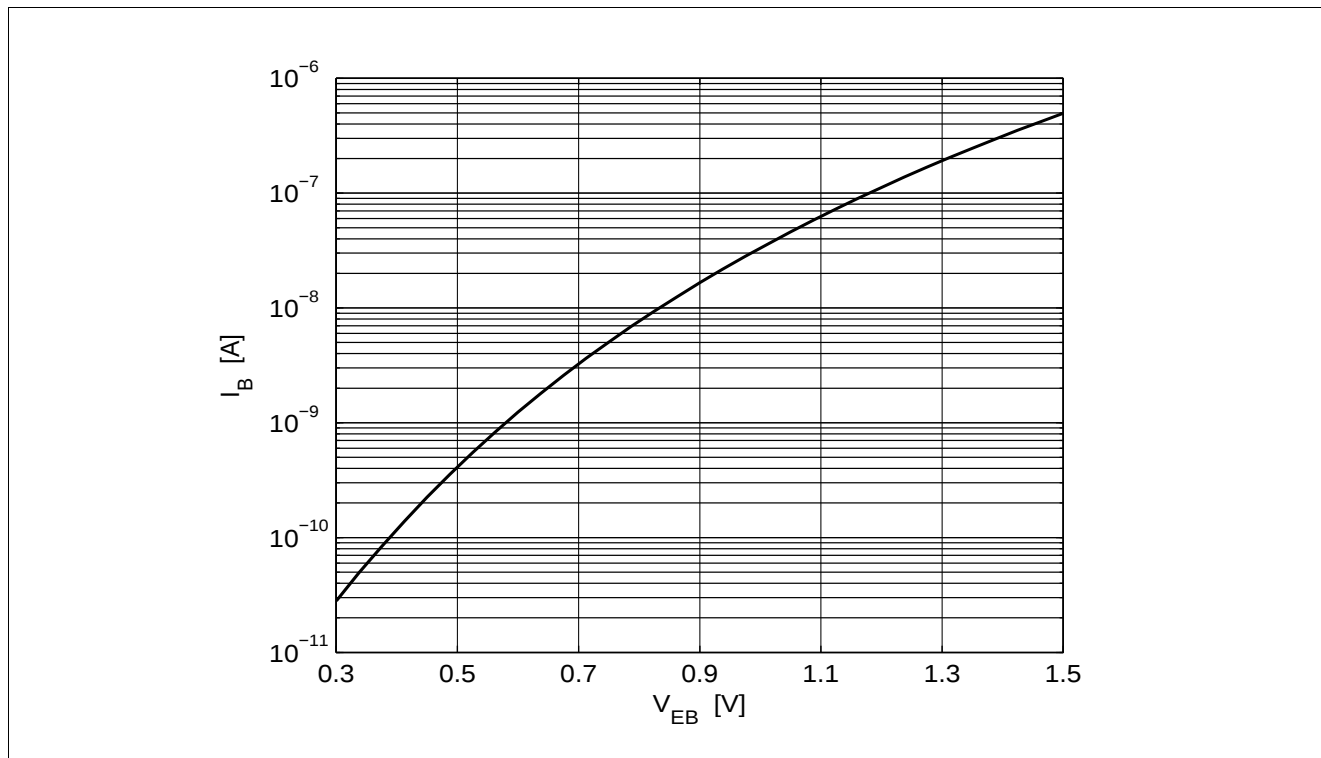


Figure 7 Base Current vs. Base Emitter Reverse Voltage $I_B = f(V_{EB})$, $V_{CE} = 3\text{ V}$

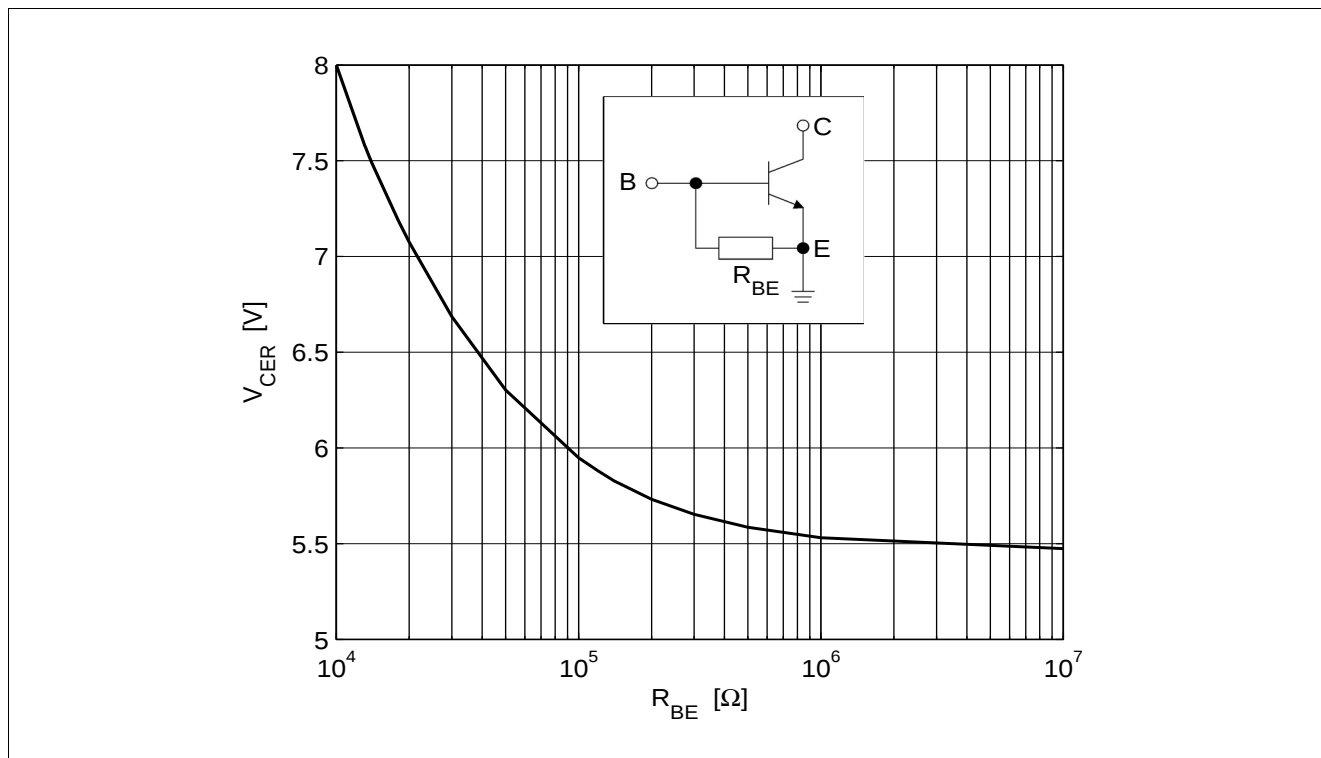


Figure 8 Collector Emitter Breakdown Voltage $V_{CER} = f(R_{BE})$, $I_C = 1\text{ mA}$

4.5 Characteristic AC Diagrams

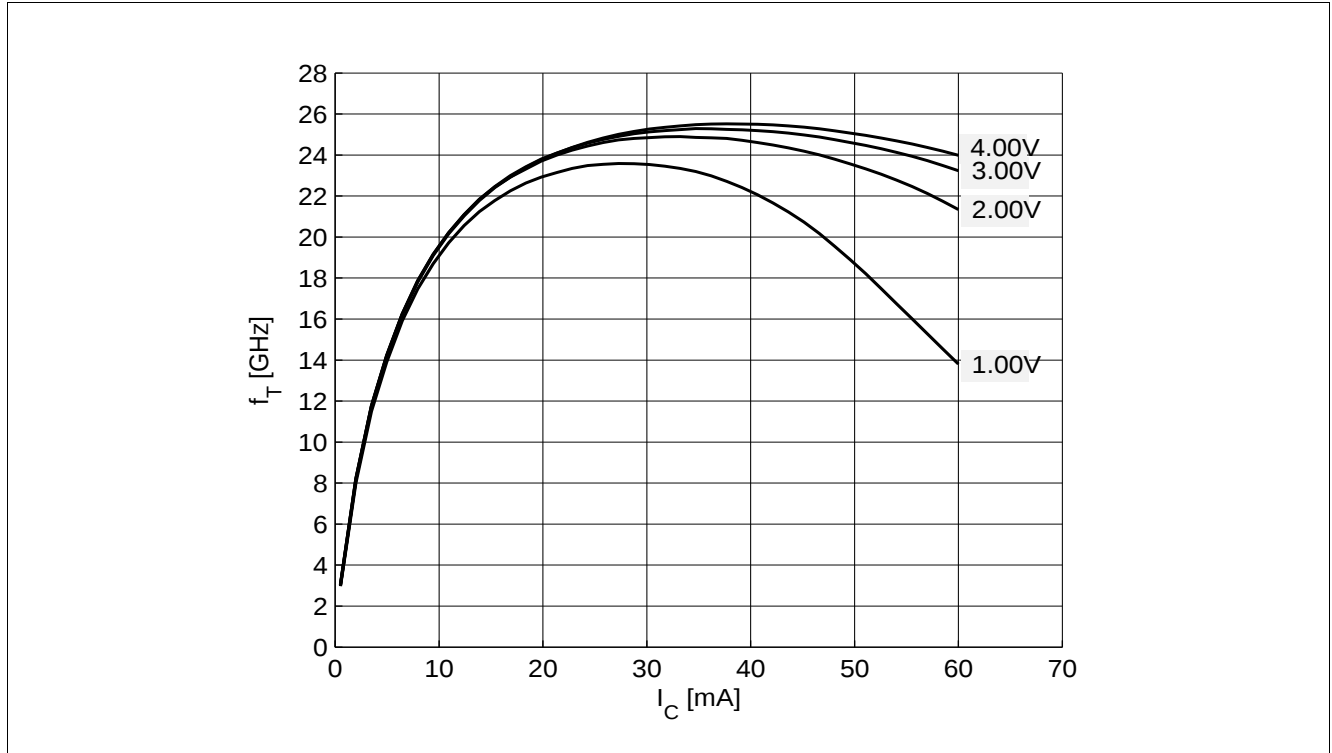


Figure 9 Transition Frequency $f_T = f(I_C)$, $f = 2$ GHz, $V_{CE} = \text{Parameter}$

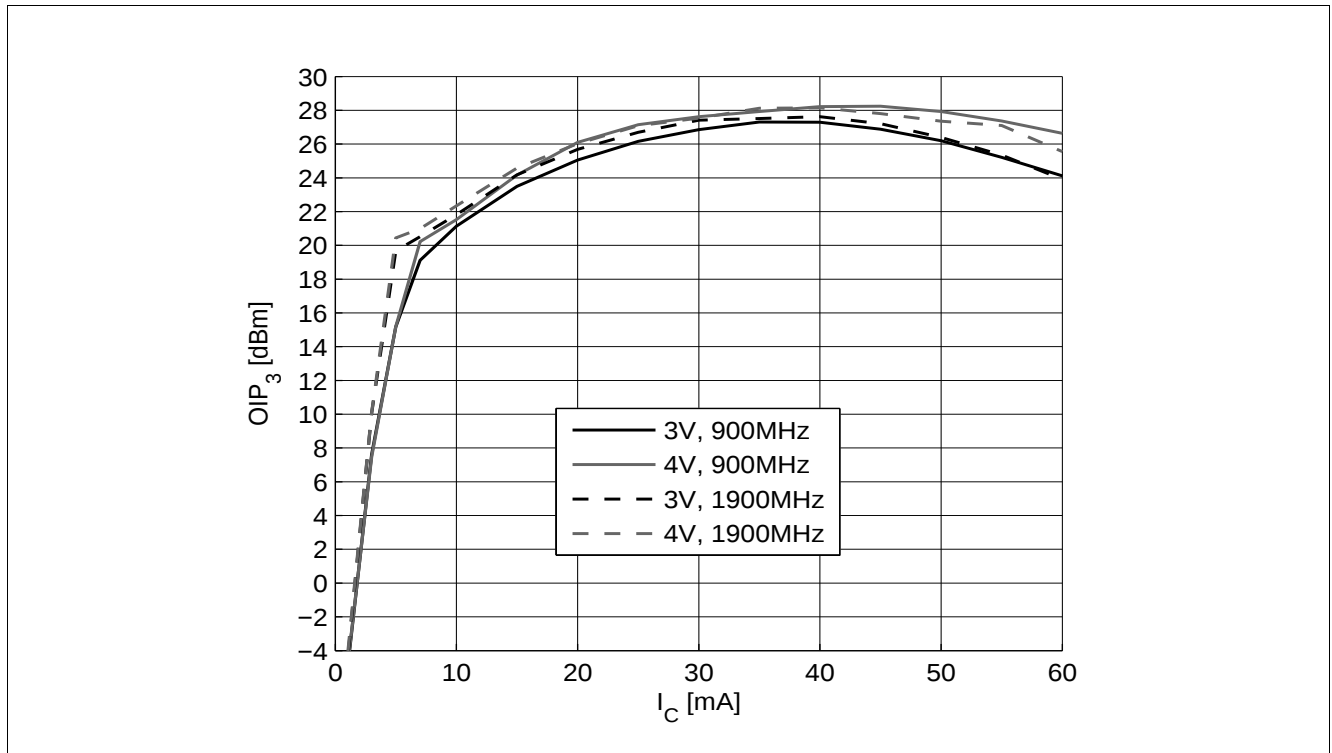


Figure 10 3rd Order Intercept Point $OIP_3 = f(I_C)$, $Z_S = Z_L = 50 \Omega$, $V_{CE}, f = \text{Parameters}$

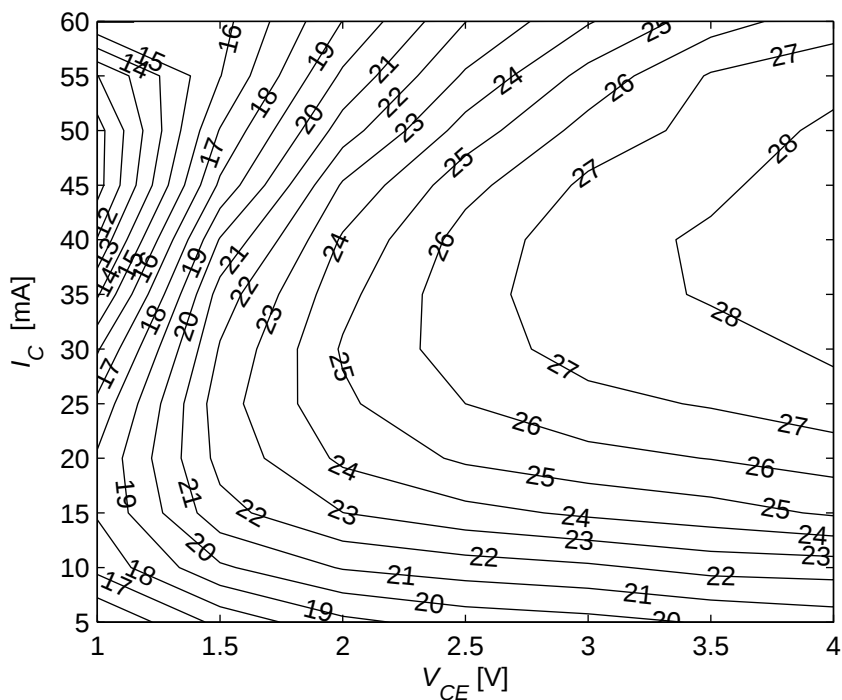


Figure 11 3rd Order Intercept Point at output OIP_3 [dBm] = $f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 1900$ MHz

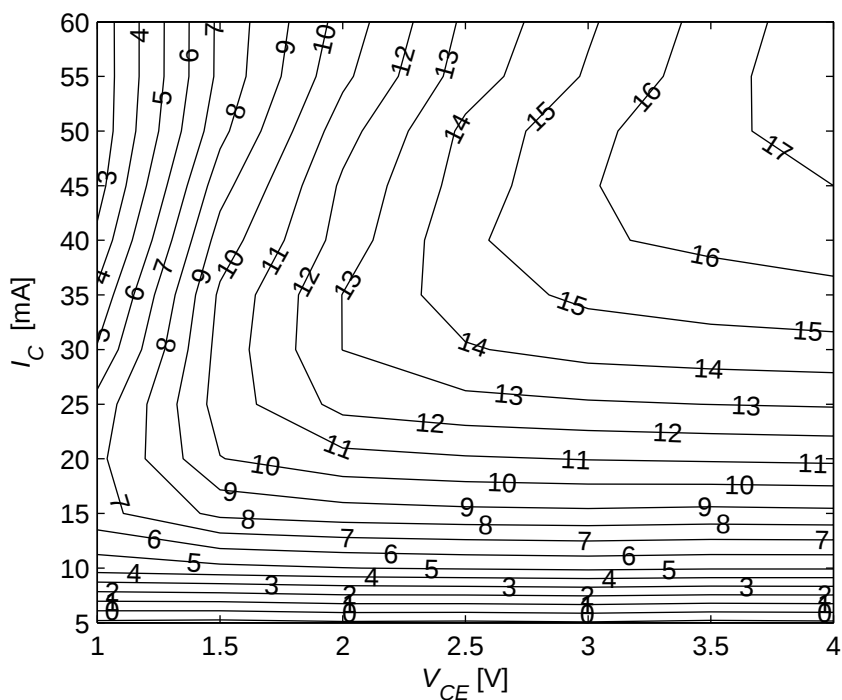


Figure 12 Compression Point at output OP_{1dB} [dBm] = $f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 1900$ MHz

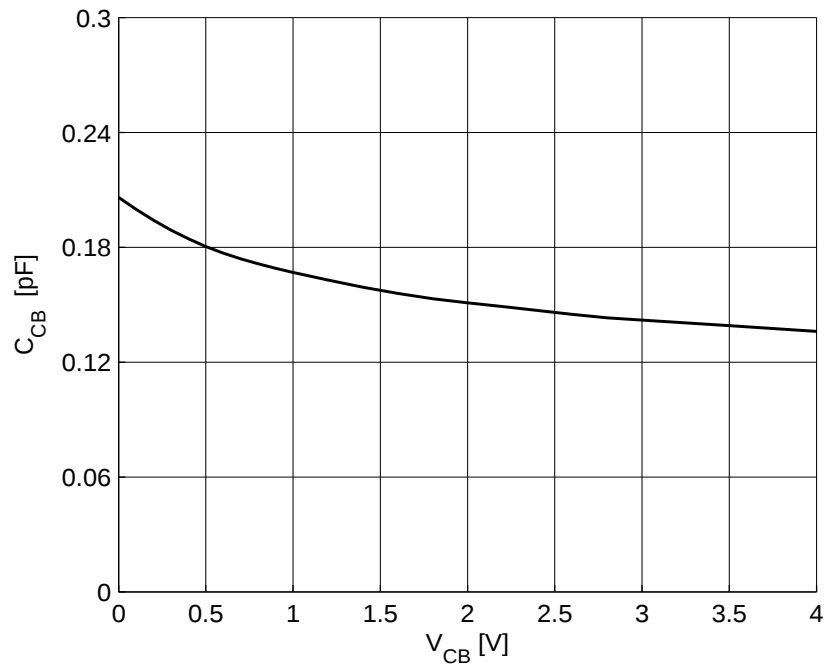


Figure 13 Collector Base Capacitance $C_{CB} = f(V_{CB})$, $f = 1$ MHz

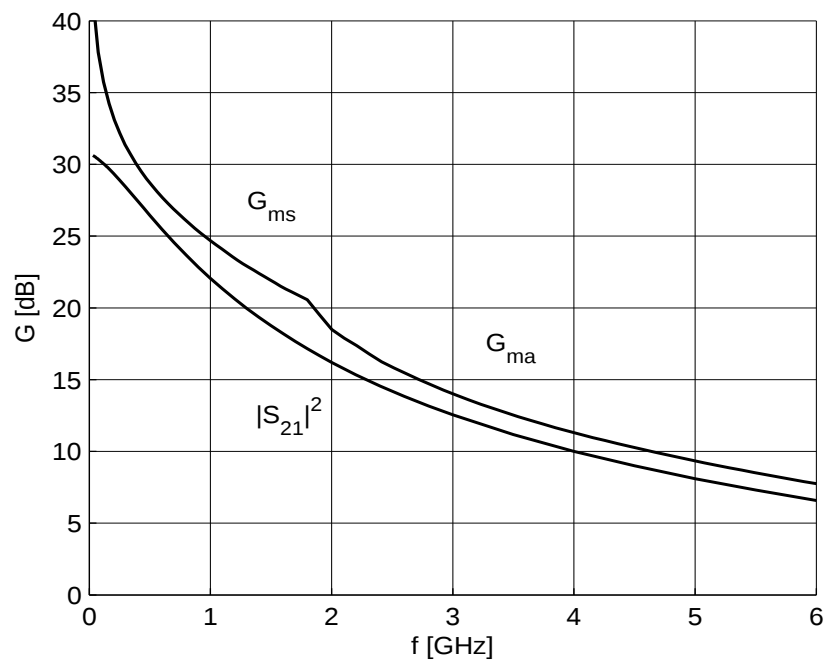


Figure 14 Gain G_{ma} , G_{ms} , $|S_{21}|^2 = f(f)$, $V_{CE} = 3$ V, $I_C = 15$ mA

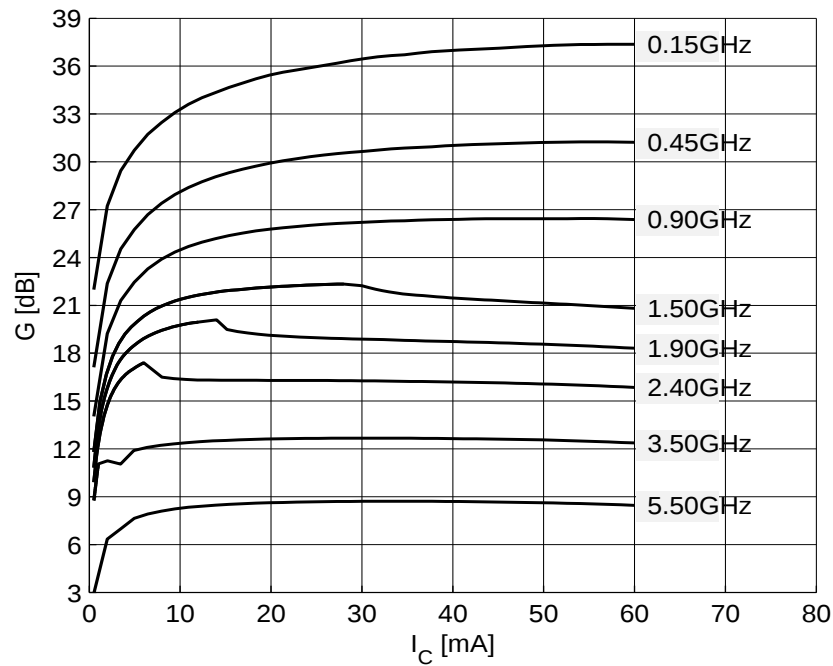


Figure 15 Maximum Power Gain $G_{\max} = f(I_C)$, $V_{CE} = 3\text{ V}$, $f = \text{Parameter in GHz}$

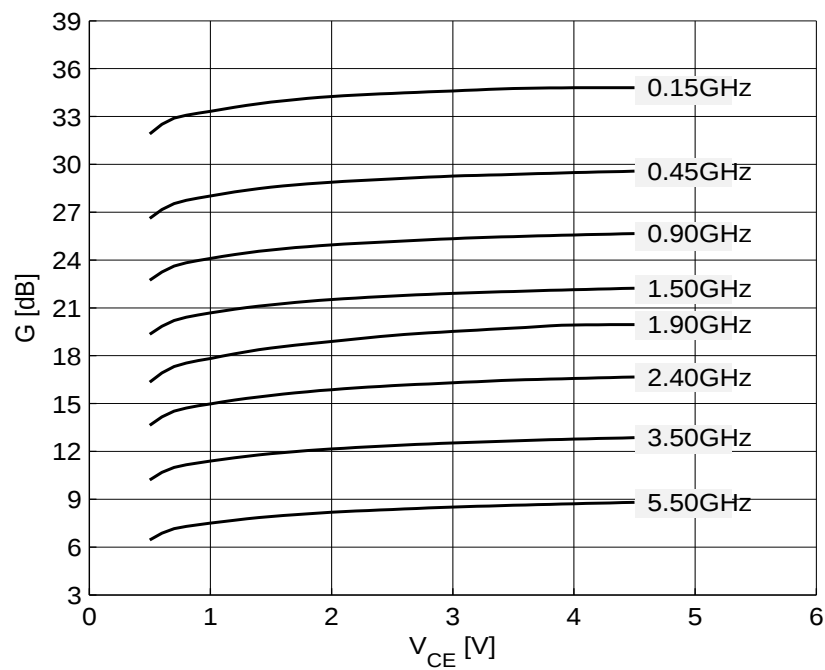


Figure 16 Maximum Power Gain $G_{\max} = f(V_{CE})$, $I_C = 15\text{ mA}$, $f = \text{Parameter in GHz}$

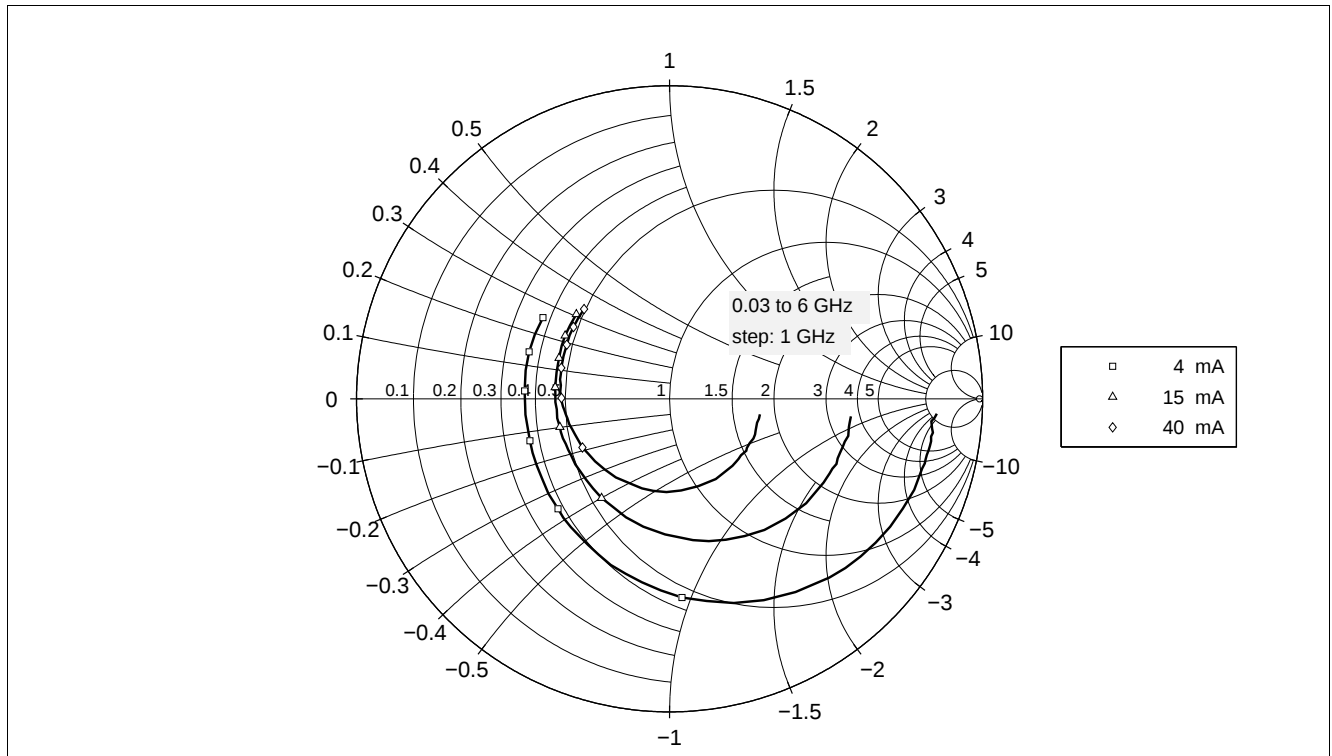


Figure 17 Input Matching $S_{11} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 / 45 \text{ mA}$

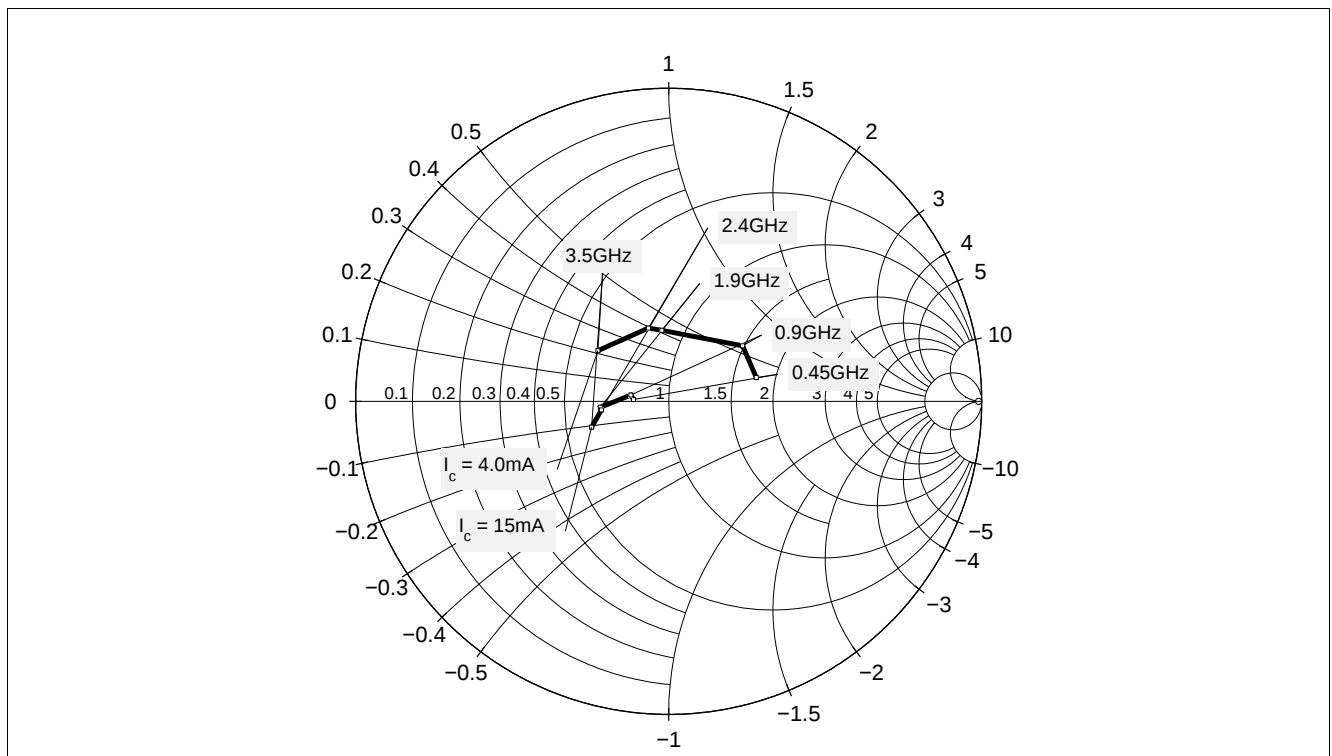


Figure 18 Source Impedance for Minimum Noise Figure $Z_{opt} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 \text{ mA}$

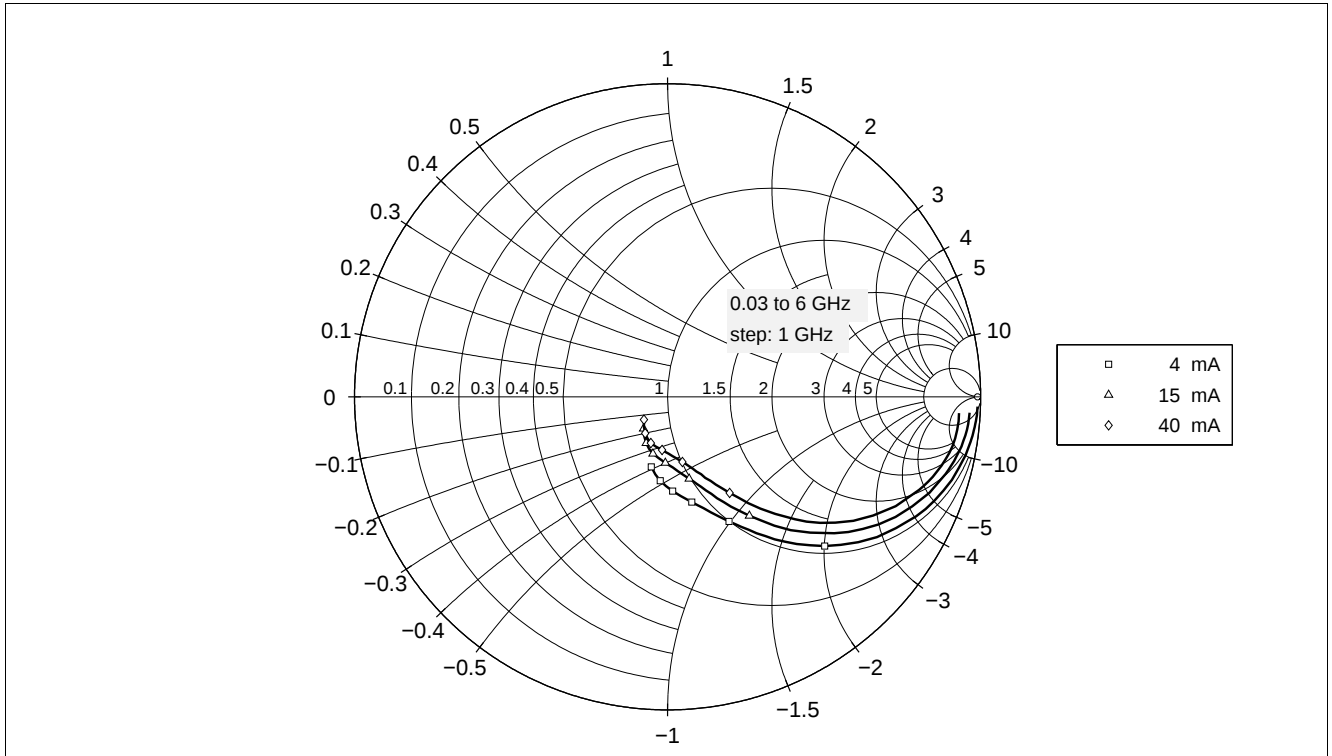


Figure 19 Output Matching $S_{22} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 / 45 \text{ mA}$

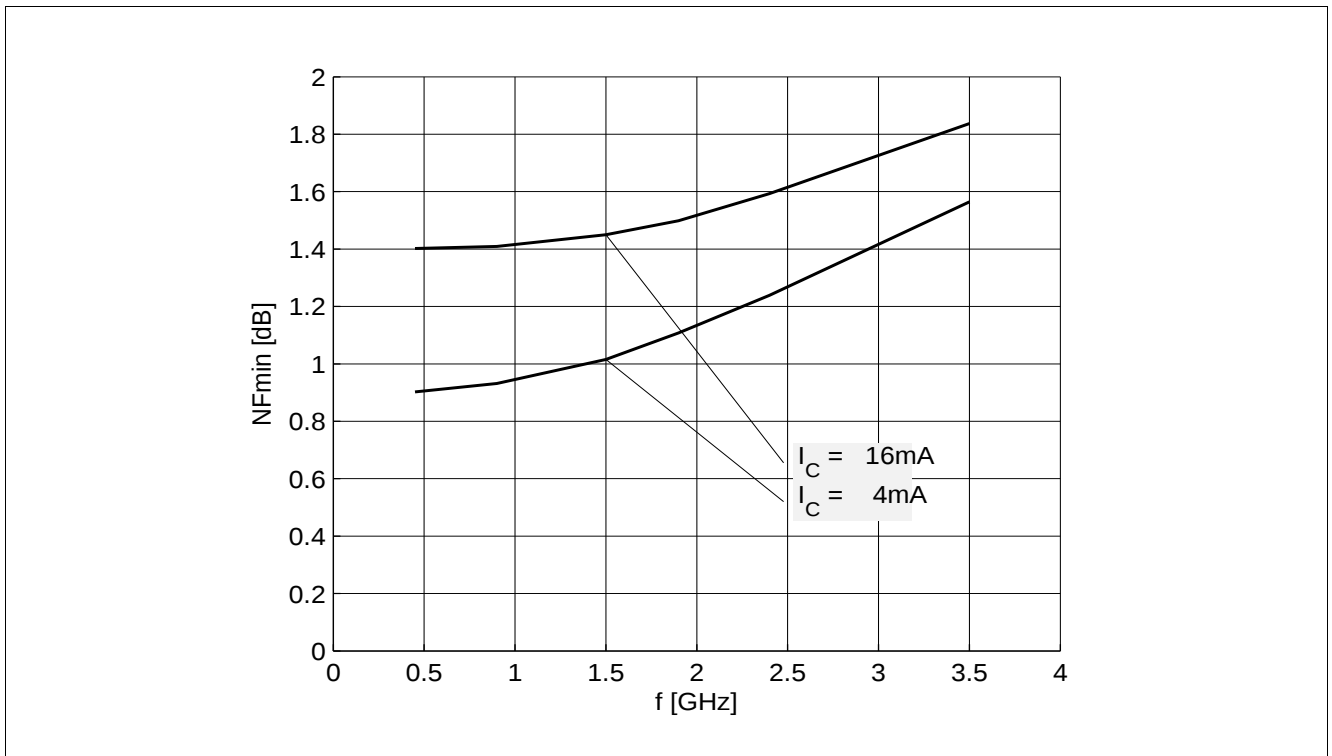


Figure 20 Noise Figure $NF_{min} = f(f)$, $V_{CE} = 3 \text{ V}$, $I_C = 4 / 15 \text{ mA}$, $Z_S = Z_{opt}$

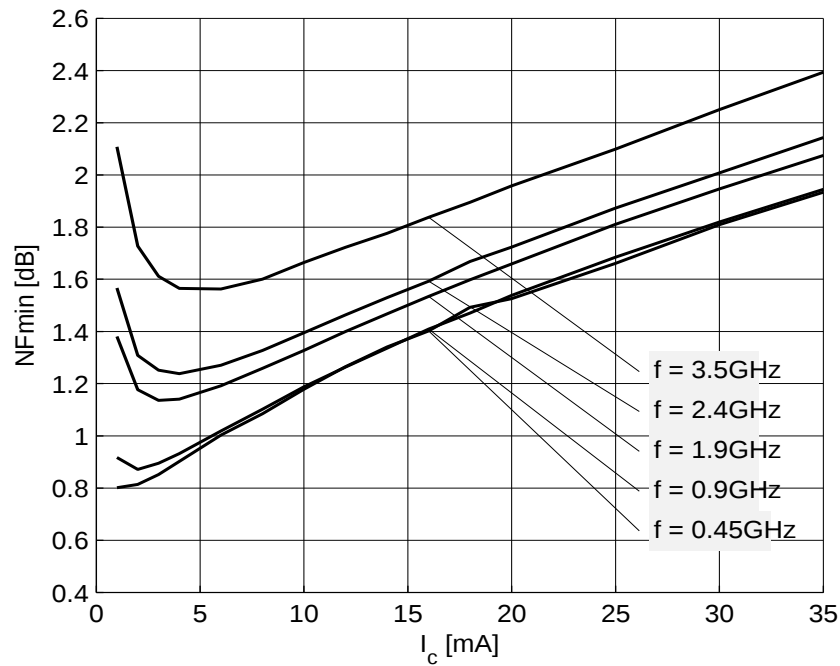


Figure 21 Noise Figure $NF_{min} = f(I_C)$, $V_{CE} = 3\text{ V}$, $Z_S = Z_{opt}$, $f = \text{Parameter in GHz}$

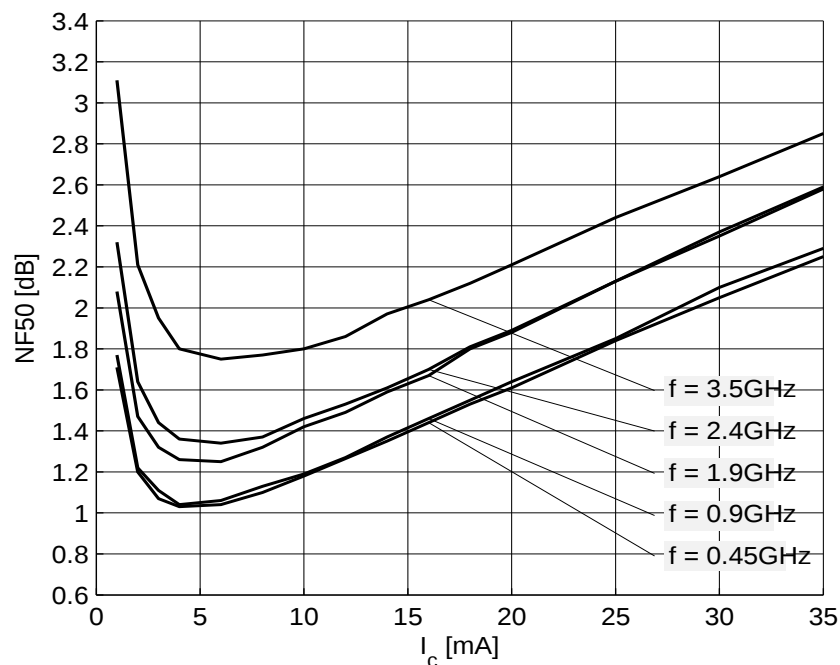


Figure 22 Noise Figure $NF_{50} = f(I_C)$, $V_{CE} = 3\text{ V}$, $Z_S = 50\ \Omega$, $f = \text{Parameter in GHz}$

Note: The curves shown in this chapter have been generated using typical devices but shall not be considered as a guarantee that all devices have identical characteristic curves. $T_A = 25\text{ }^\circ\text{C}$.

5 Simulation Data

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please consult our website and download the latest versions before actually starting your design.

You find the BFP420F SPICE GP model on the official homepage of Infineon RF transistors in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC- and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device.

The model parameters have been extracted and verified up to 10 GHz using typical devices. The BFP420F SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.

6 Package Information TSFP-4

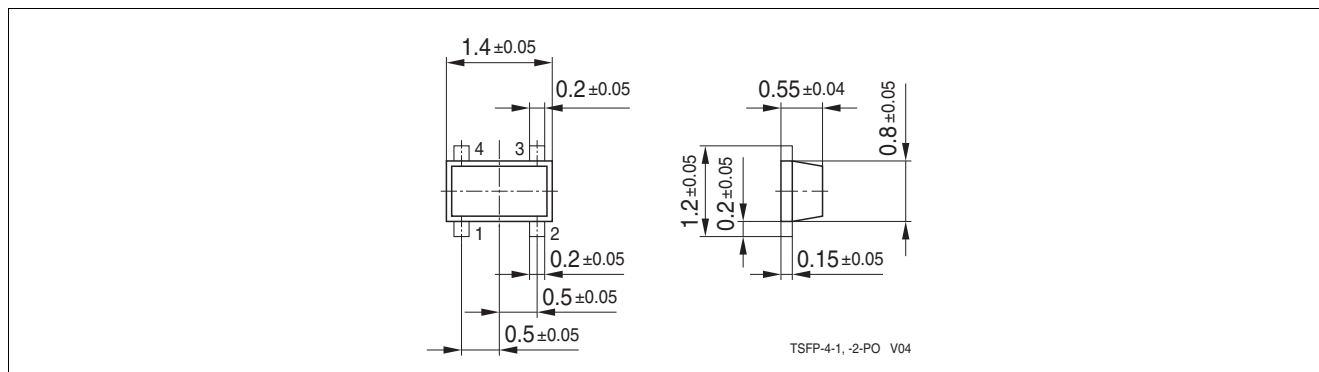


Figure 23 Package Outline

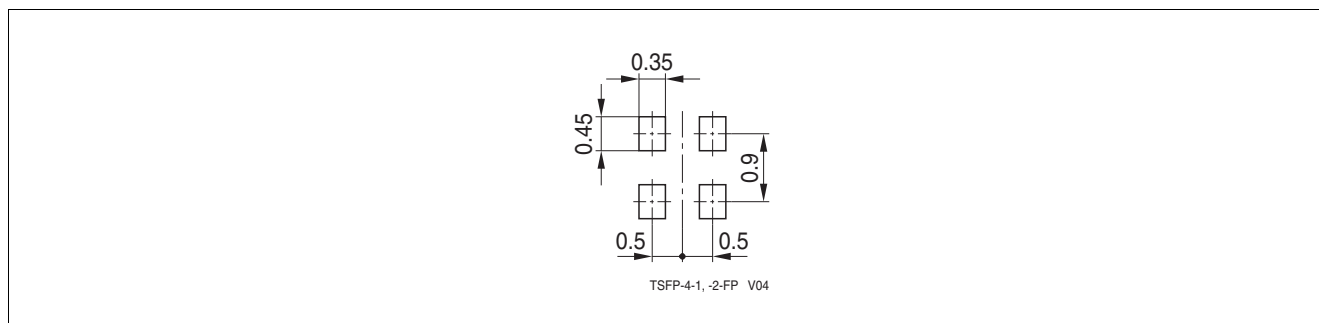


Figure 24 Package Foot Print

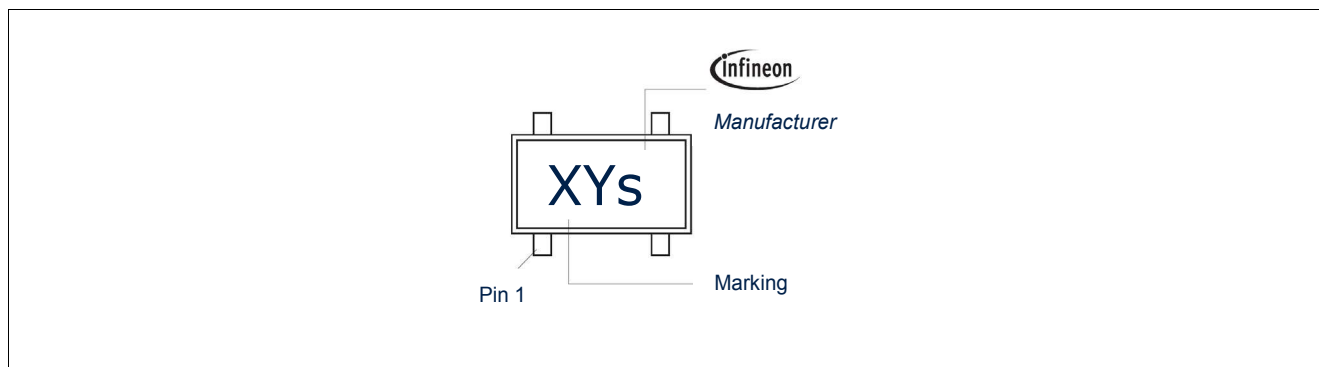


Figure 25 Marking Example (Marking BFP420F: AMs)

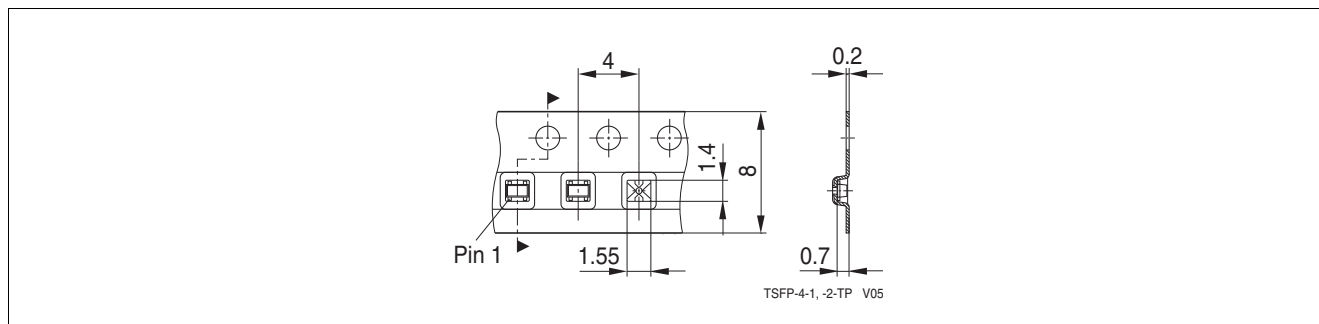


Figure 26 Tape Dimensions

www.infineon.com